

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	IS&R	L1	3	(("6503788") or ("6645799") or ("6727132")).PN.	US-PGPUB; USPAT	2004/12/09 17:06			
2	BRS	L2	3	(("5683920" "5780330" "6300184")).PN.	US-PGPUB; USPAT; USOCR	2004/12/09 17:36			
3	BRS	L3	3	(("6503788")).URPN.	USPAT	2004/12/09 17:38			
4	BRS	L4	4	(("20020110969" "5683920" "5780330" "6300184")).PN.	US-PGPUB; USPAT; USOCR	2004/12/09 17:40			
5	BRS	L5	0	(("6645799")).URPN.	USPAT	2004/12/09 17:41			
6	BRS	L6	5	(("20020110969" "5683920" "5780330" "6300184" "6503788")).PN.	US-PGPUB; USPAT; USOCR	2004/12/09 17:42			
7	BRS	L7	0	(("6727132")).URPN.	USPAT	2004/12/09 17:42			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	11534	CMOS or "CMOS" or (complementary adj metal adj oxide adj semiconductor\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:10			
9	BRS	L9	19807	(doped near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (p- type or (p adj type) or boron or (boron adj (fluoride or difluoride)) or BF2 or "BF2" or "BF.sub.2" or B or "B")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:12			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BRS	L10	35941	((dop\$4 or implant\$8 or introduc\$4 or inject\$4) near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (p-type or (p adj type) or boron or (boron adj (fluoride or difluoride)) or BF2 or "BF2" or "BF.sub.2" or B or "B")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:23			
11	BRS	L11	60392	(metal\$5 or titanium or tungsten) near3 nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:13			
12	BRS	L12	1088418	WN? or WN or TiN or TiN? or "TiN" or "WN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:14			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L13	264217	(anneal\$4 or heat\$4) with (nitrogen or hydrogen or N2 or "N2" or "N.sub.2" or H2 or "H2" or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:16			
14	IS&R	L14	2321	((438/199) or (438/216) or (438/223) or (438/224) or (438/227) or (438/228) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.	US-PGPUB; USPAT; USOCR	2004/12/09 19:16			
15	BRS	L15	1126709	11 or 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:20			
16	BRS	L16	4957615	15 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:21			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L17	2186	16 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:21			
18	BRS	L18	38254	((dop\$4 or implant\$8 or introduc\$4 or inject\$4) near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (n-type or (n adj type) or phosphorus or phosphorous or arsenic or antimony)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:25			
19	BRS	L19	1655	17 and 18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:26			
20	BRS	L20	745	19 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 19:34			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L21	519	20 and (@ad<="20000816" or @rlad<="20000816")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 20:03			

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	((("6503788") or ("6645799") or ("6727132"))).PN.	US-PGPUB; USPAT	OR	OFF	2004/12/09 17:06
L2	3	("5683920" "5780330" "6300184").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/09 17:36
L3	3	("6503788").URPN.	USPAT	OR	OFF	2004/12/09 17:38
L4	4	("20020110969" "5683920" "5780330" "6300184").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/09 17:40
L5	0	("6645799").URPN.	USPAT	OR	OFF	2004/12/09 17:41
L6	5	("20020110969" "5683920" "5780330" "6300184" "6503788").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/09 17:42
L7	0	("6727132").URPN.	USPAT	OR	OFF	2004/12/09 17:42
L8	115344	CMOS or "CMOS" or (complementary adj metal adj oxide adj semiconductor\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:10
L9	19807	(doped near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (p-type or (p adj type) or boron or (boron adj (fluoride or difluoride)) or BF2 or "BF2" or "BF.sub.2" or B or "B")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:12
L10	35941	((dop\$4 or implant\$8 or introduc\$4 or inject\$4) near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (p-type or (p adj type) or boron or (boron adj (fluoride or difluoride)) or BF2 or "BF2" or "BF.sub.2" or B or "B")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:23
L11	60392	(metal\$5 or titanium or tungsten) near3 nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:13
L12	1088418	WN? or WN or TiN or TiN? or "TiN" or "WN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:14

L13	264217	(anneal\$4 or heat\$4) with (nitrogen or hydrogen or N2 or "N2" or "N.sub.2" or H2 or "H2" or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:16
L14	2321	((438/199) or (438/216) or (438/223) or (438/224) or (438/227) or (438/228) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/09 19:16
L15	1126709	11 or 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:20
L16	49576	15 and 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:21
L17	2186	16 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:21
L18	38254	((dop\$4 or implant\$8 or introduc\$4 or inject\$4) near10 (amorphous or silicon or polysilicon or poly or polycrystalline)) with (n-type or (n adj type) or phosphorus or phosphorous or arsenic or antimony)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:25
L19	1655	17 and 18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:26
L20	745	19 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 19:34

L21	519	20 and (@ad<="20000816" or @rlad<="20000816")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 20:23
L22	226	20 not 21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/09 20:23